

ABSTRACT**SILICON SINGLE CRYSTAL PRODUCTION METHOD**

5 The silicon single crystal production method includes steps of
growing the straight-body section 4 of the silicon single
crystal 2 under the influence of the horizontal magnetic field
with a magnetic flux density at its magnetic center L2 being
equal to or more than 1000 Gauss, and equal to or less than 2000
10 Gauss, then reducing the relative lifting speed of the silicon
single crystal to the surface of the melt 32 to 0 mm/minute,
then maintaining the static state until there is a decrease in
the apparent weight of the silicon single crystal, then further
maintaining the static state so that the whole growth front of
15 the silicon single crystal will form a convex shape protruding
in the opposite direction to the lifting direction of the
silicon single crystal, and finally separating the silicon
single crystal from the melt.

20 Fig. 2